

ZXTEM322

MPPS™ Miniature Package Power Solutions

80V NPN LOW SATURATION TRANSISTOR

SUMMARY

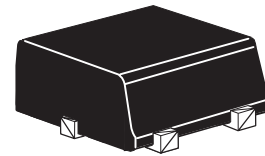
NPN — $V_{CE0} = 80V$; $R_{SAT} = 68m\Omega$; $I_C = 3.5A$

DESCRIPTION

Packaged in the new innovative 2mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual PNP transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other **key benefits**:

Performance capability equivalent to much larger packages
Improved circuit efficiency & power levels
PCB area and device placement savings
Lower Package Height (0.9mm nom)
Reduced component count



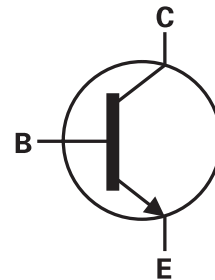
MLP322

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (**185mV max @1A**)
- h_{FE} specified up to 5A
- $I_C = 3.5A$ Continuous Collector Current
- 2mm x 2mm MLP

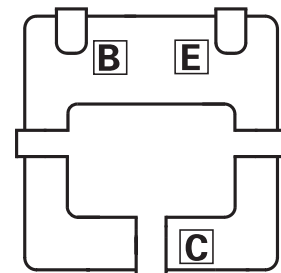
APPLICATIONS

- DC - DC Converters
- DC - DC Modules
- Power switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTEM322TA	7"	8mm	3000
ZXTEM322TC	13"	8mm	10000



Underside View

DEVICE MARKING

- SE

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	7.5	V
Peak Pulse Current	I_{CM}	5	A
Continuous Collector Current ^(a)	I_C	3.5	A
Base Current	I_B	1000	mA
Power Dissipation at $T_A=25^{\circ}\text{C}$ ^(a) Linear Derating Factor	P_D	1.5 12	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ ^(b) Linear Derating Factor	P_D	2.45 19.6	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ ^(d) Linear Derating Factor	P_D	1 8	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ ^(e) Linear Derating Factor	P_D	3 24	W mW/ $^{\circ}\text{C}$
Operating & Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

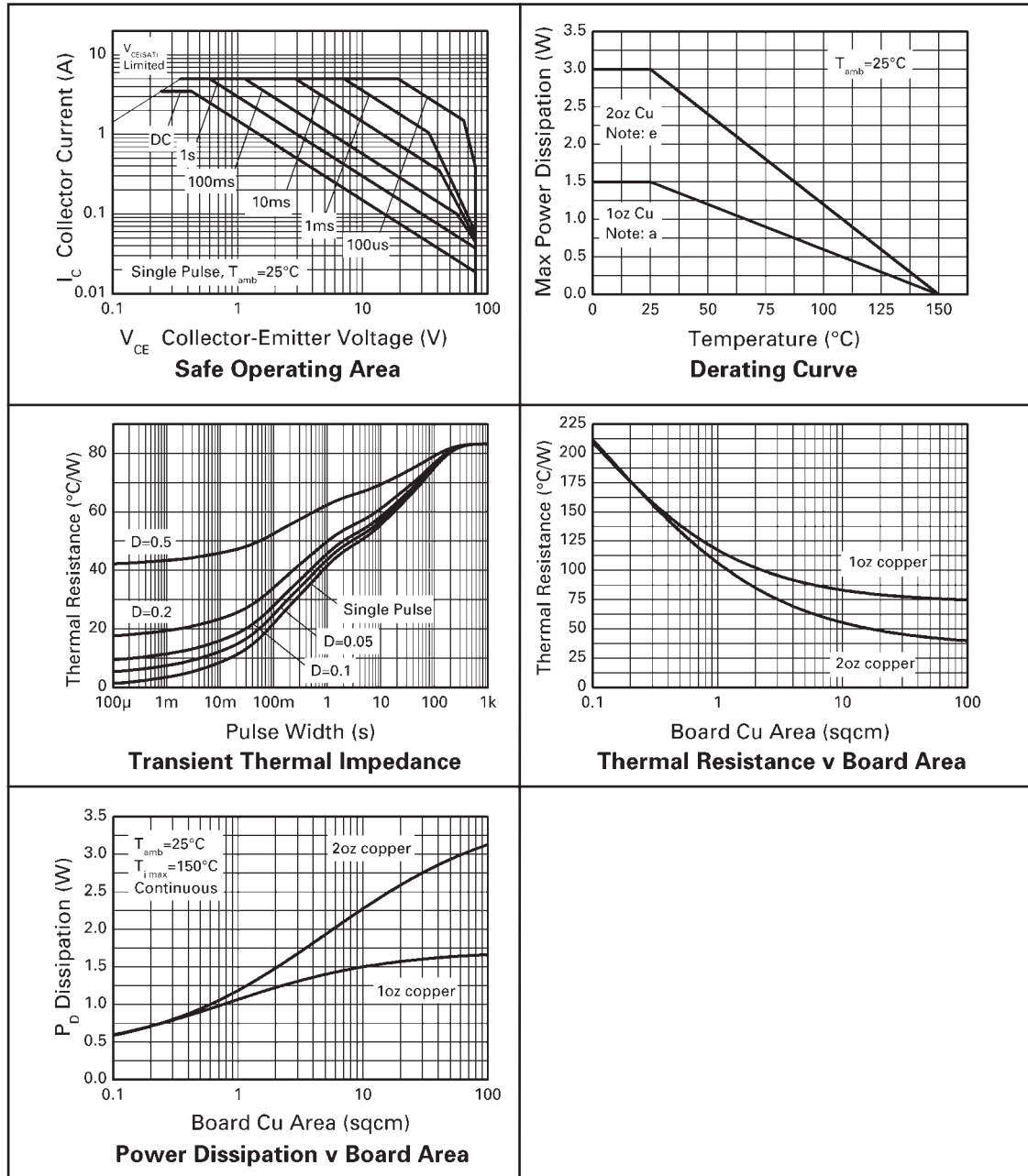
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	83	$^{\circ}\text{C/W}$
Junction to Ambient ^(b)	$R_{\theta JA}$	51	$^{\circ}\text{C/W}$
Junction to Ambient ^(d)	$R_{\theta JA}$	125	$^{\circ}\text{C/W}$
Junction to Ambient ^(e)	$R_{\theta JA}$	42	$^{\circ}\text{C/W}$

NOTES

- (a) For a single device surface mounted on 10 sq cm 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**.
- (b) For a single device surface mounted on 10 sq cm 1oz copper on FR4 PCB, in still air conditions measured at $t \leq 5$ secs **with all exposed pads attached**.
- (c) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (d) For a single device surface mounted on 10 sq cm 1oz copper FR4 PCB, in still air conditions **with minimal lead connections only**.
- (e) For a single device surface mounted on 65 sq cm 2oz copper FR4 PCB, in still air conditions **with all exposed pads attached**.
- (f) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device, as shown in the package dimensions data. The thermal resistance for a device mounted on 1.5mm thick FR4 board using minimum copper of 1oz weight and 1mm wide tracks is $R_{th} = 300^{\circ}\text{C/W}$ giving a power rating of $P_{tot} = 420\text{mW}$.

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TYPICAL CHARACTERISTICS



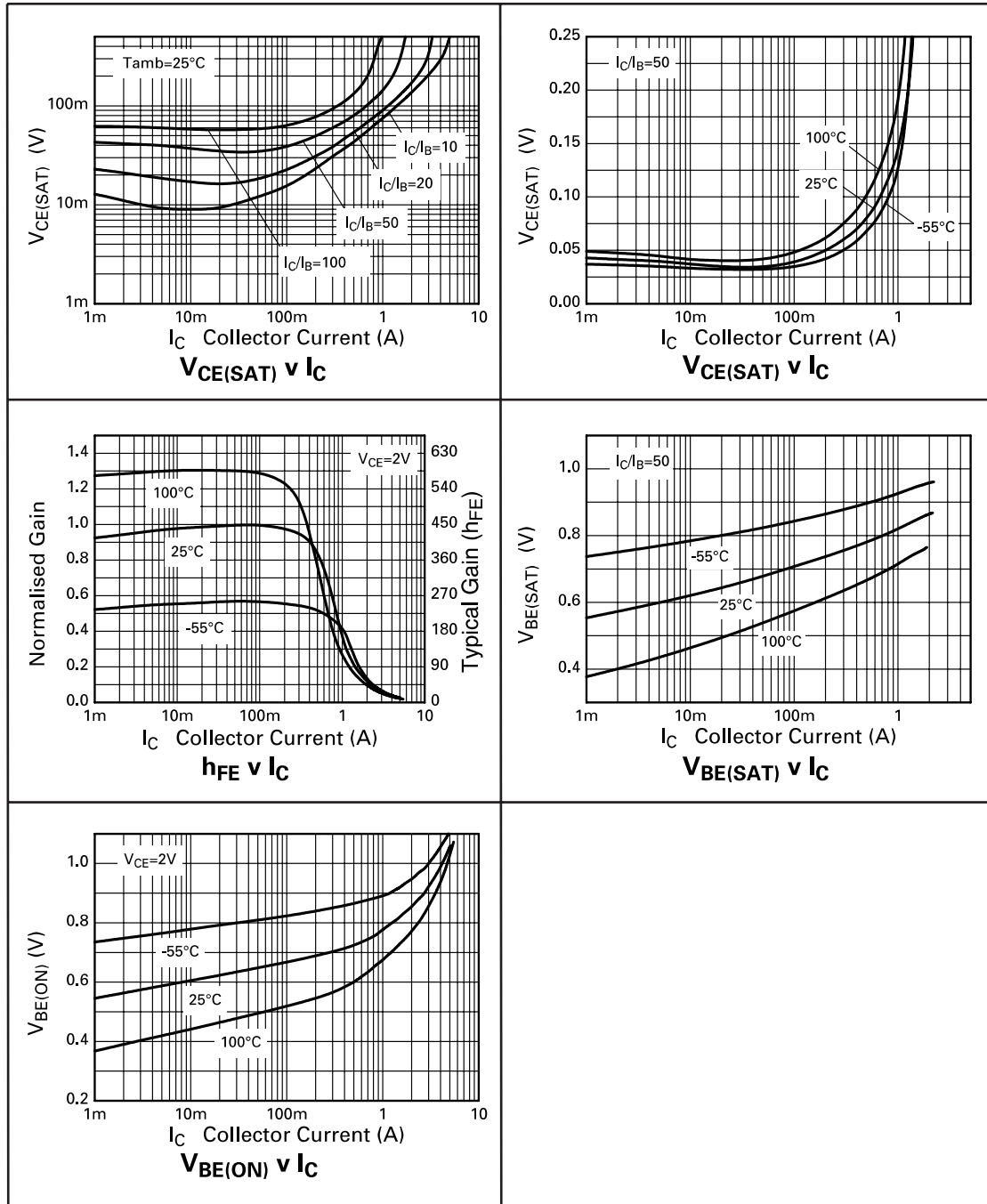
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100	180		V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	110		V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.2		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			25	nA	$V_{CB} = 80\text{V}$
Emitter Cut-Off Current	I_{EBO}			25	nA	$V_{EB} = 6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			25	nA	$V_{CE} = 65\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		15 45 145 160 240	20 60 185 200 325	mV mV mV mV mV	$I_C = 0.1\text{A}, I_B = 10\text{mA}^*$ $I_C = 0.5\text{A}, I_B = 50\text{mA}^*$ $I_C = 1\text{A}, I_B = 20\text{mA}^*$ $I_C = 1.5\text{A}, I_B = 50\text{mA}^*$ $I_C = 3.5\text{A}, I_B = 300\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.09	1.175	V	$I_C = 3.5\text{A}, I_B = 300\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.96	1.05	V	$I_C = 3.5\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200 300 110 60 20	450 450 170 90 30 10	900		$I_C = 10\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 200\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 1.5\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 3\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 5\text{A}, V_{CE} = 2\text{V}^*$
Transition Frequency	f_T	100	160		MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		11.5	18	pF	$V_{CB} = 10\text{A}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		86		ns	$V_{CC} = 10\text{V}, I_C = 1\text{A}$
Turn-Off Time	$t_{(off)}$		1128		ns	$I_{B1} = I_{B2} = 25\text{mA}$

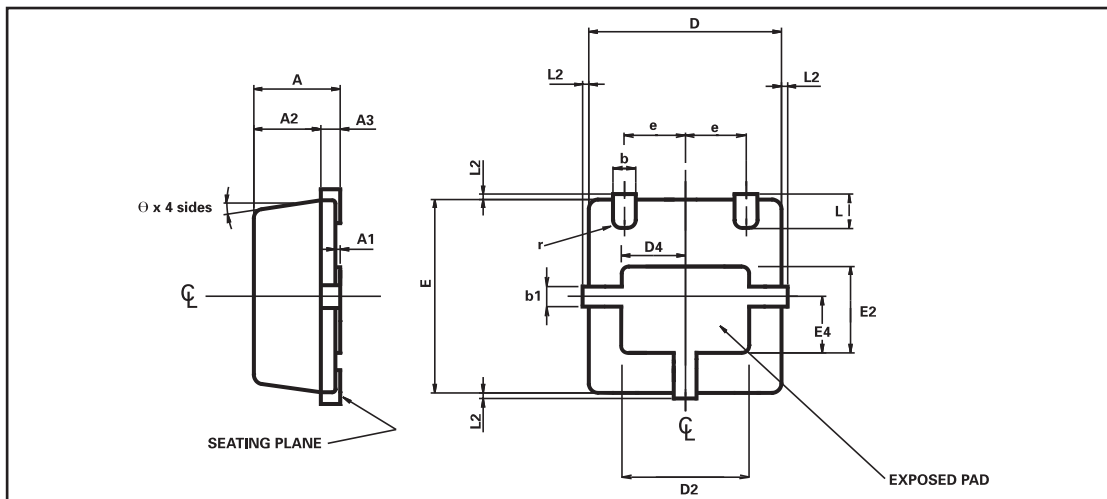
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



Controlling dimensions are in millimetres. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimetres		Inches		DIM	Millimetres		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.80	1.00	0.0315	0.0393	e	0.65 REF		0.0255 REF	
A1	0.00	0.05	0.00	0.002	E	2.00 BSC		0.0787 BSC	
A2	0.65	0.75	0.0255	0.0295	E2	0.79	0.99	0.031	0.039
A3	0.15	0.25	0.0059	0.0098	E4	0.48	0.68	0.0188	0.0267
b	0.18	0.28	0.0070	0.0110	L	0.20	0.45	0.0078	0.0177
b1	0.17	0.30	0.0066	0.0118	L2	0.125 MAX.		0.005 REF	
D	2.00 BSC		0.0787 BSC		r	0.075 BSC		0.0029 BSC	
D2	1.22	1.42	0.0480	0.0559	Θ	0°	12°	0°	12°
D4	0.56	0.76	0.0220	0.0299					

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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